TOSHIBA Photocoupler GaAℓAs Ired & Photo−Diode Array

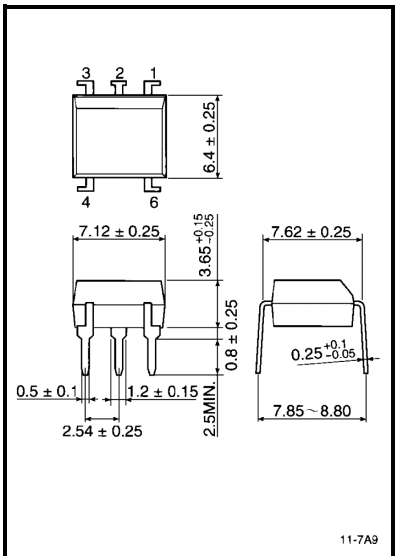
TLP590B

Telecommunication
Programmable Controllers
Mos Gate Driver
MOS FET Gate Driver

The TOSHIBA TLP590B consists of an aluminum galium arsenide infrared emitting diode optically coupled to a series connected photo−diode array in a six lead plastic DIP package.
TLP590B is suitable for MOS FET gate driver.

- UL recognized: UL1577, file No. E67349

Unit in mm



TOSHIBA 11−7A9

Weight: 0.39g

Short Current

Type Name	Classification	Short Current		Marking Of Classification
		(min.)	I_F	
TLP590B	C20	20μA	10mA	20
	Standard	12μA		20, blank

(Note) Application type name for certification test, please use standard product type name, i.e.

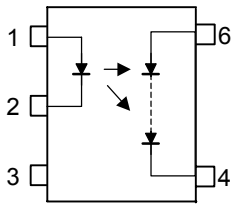
TLP590B(C20): TLP590B

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
LED	Forward current	I_F	50	mA
	Forward current derating (Ta ≥ 25°C)	ΔI_F / °C	−0.5	mA / °C
	Pulse forward current (100μs pulse, 100 pps)	I_{FP}	1	A
	Reverse voltage	V_R	3	V
	Junction temperature	T_j	125	°C
Detector	Foward current	I_{FD}	50	μA
	Reverse voltage	V_{RD}	10	V
	Junction temperature	T_j	125	°C
Storage temperature range		T_{stg}	−55~125	°C
Operating temperature range		T_{opr}	−40~85	°C
Lead soldering temperature (10sec.)		T_{sol}	260	°C
Isolation voltage (AC, 1 min., R.H. ≤ 60%) (Note 1)		BV_S	2500	Vrms

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together, and pins 4 and 6 shorted together.

Pin Configuration(top view)



1. : Anode
2. : Cathode
3. : NC
4. : Cathode
6. : Anode

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Forward current	I_F	—	20	25	mA
Operating temperature	T_{opr}	−25	—	85	°C

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	I_F = 10 mA	1.2	1.4	1.7	V
	Reverse current	I_R	V_R = 3 V	—	—	10	μA
	Capacitance	C_T	V = 0, f = 1 MHz	—	30	60	pF
Detector	Forward voltage	V_{FD}	I_{FD} = 10 μA	—	7	—	V
	Reverse current	I_{RD}	V_{RD} = 10 V	—	1	—	nA
	Capacitance (anode to cathode)	C_{TD}	V = 0, f = 1 MHz	—	—	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Open voltage	V_{OC}	I_F = 10 mA	7.0	8.0	—	V
Short current	I_{SC}	I_F = 10 mA	12	20	—	μA

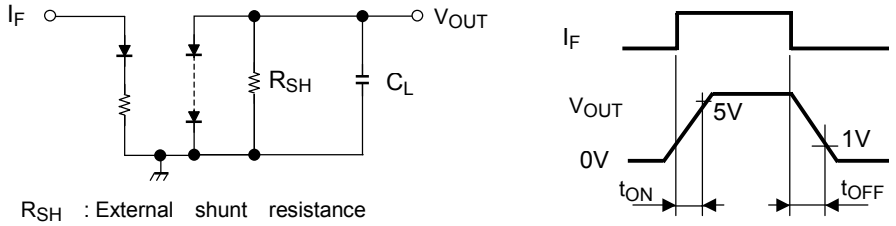
Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance input to output	C_S	V_S = 0, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	V_S = 500 V, R.H. ≤ 60%	5×10^{10}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 1 minute	2500	—	—	Vrms
		AC, 1 second in oil	—	5000	—	
		DC, 1 minute in oil	—	5000	—	Vdc

Switching Characteristics (Ta = 25°C)

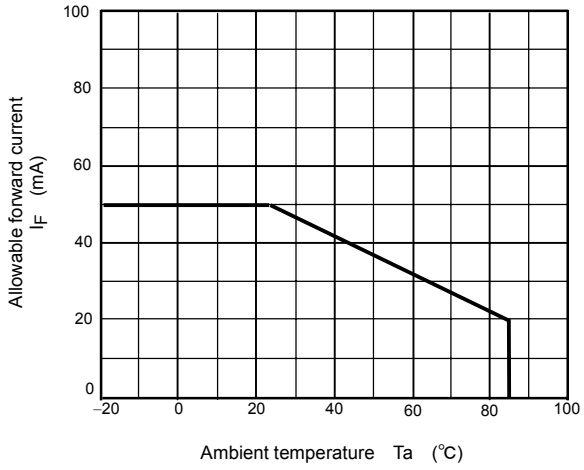
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Turn−on time	t_{on}	I_F = 20mA, R_{SH} = 510kΩ C_L =1000pF (Fig.1)	—	0.2	—	ms
Turn−off time	t_{off}		—	1	—	ms

Fig. 1 Switching time test circuit

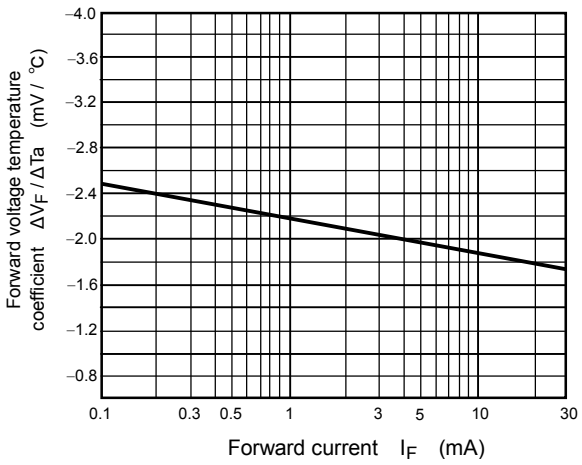


R_{SH} : External shunt resistance

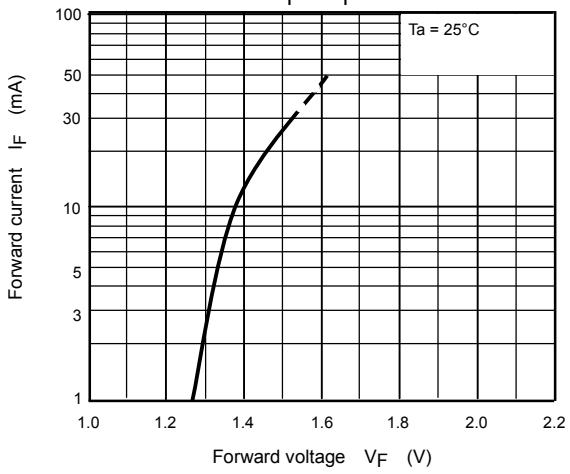
I_F – Ta



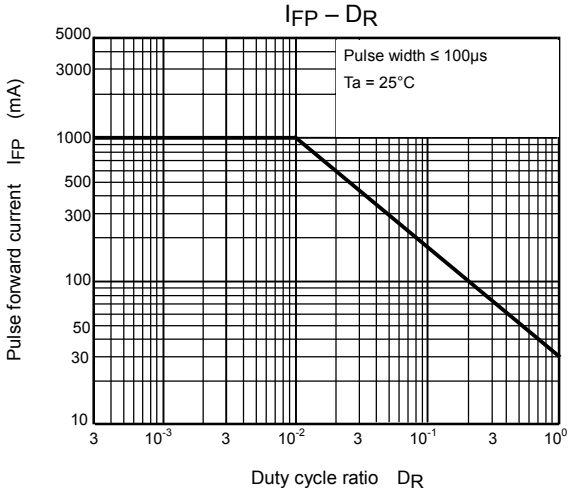
$\Delta V_F / \Delta Ta$ – I_F



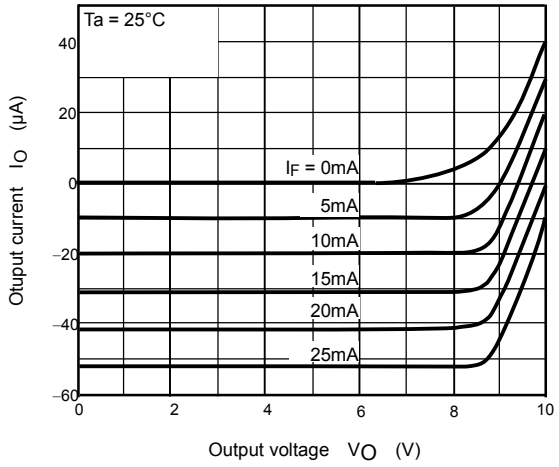
I_F – V_F



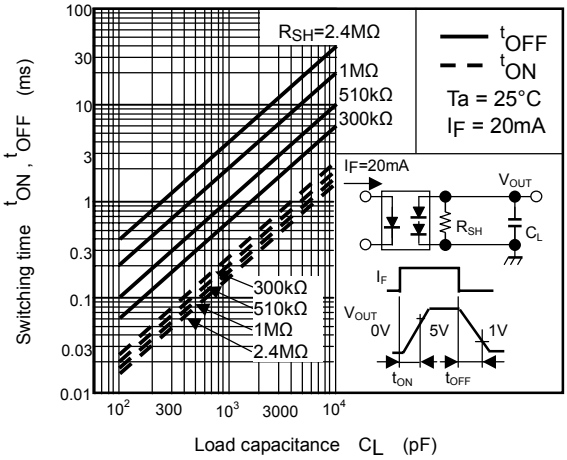
I_{FP} – D_R



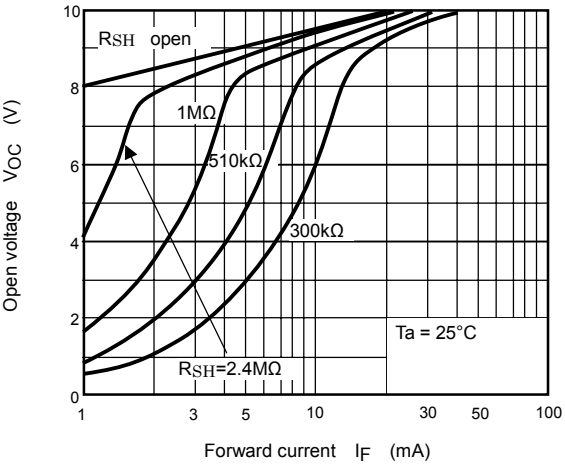
$I_O - V_O$



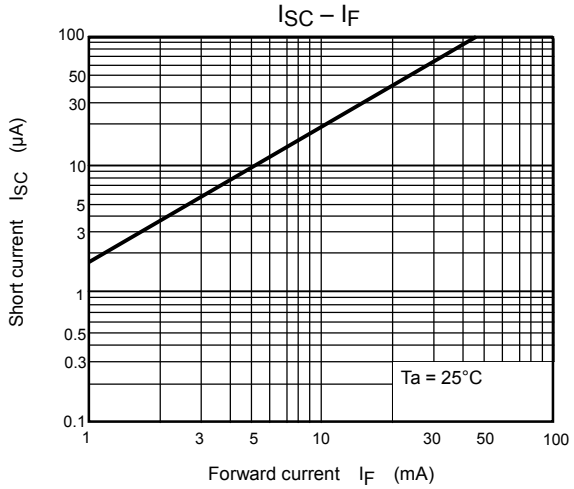
^tON , $^tOFF - C_L$



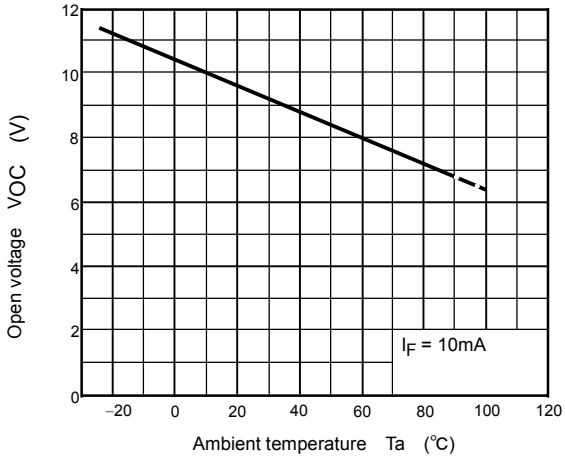
$V_{OC} - I_F$



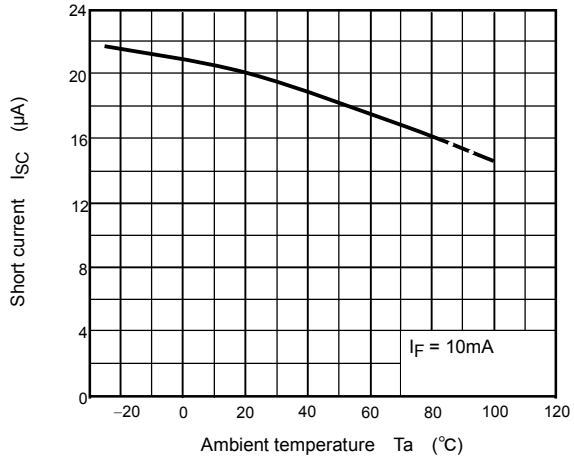
$I_{SC} - I_F$



$V_{OC} - Ta$



$I_{SC} - Ta$



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